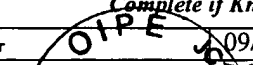


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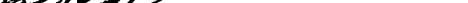
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Substitute for form 1449A/PTO				Complete if Known Application Number 09/362,192 Filing Date July 28, 1999 First Named Inventor Shunpei YAMAZAKI et al. Group Art Unit 2812 Examiner Name J. Simkovic Attorney Docket Number 740756-2011	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>					
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Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>

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8-83)U.S. Department of Commerce  
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Atty Docket 0756-2011

Serial No. 09/362,192






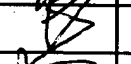





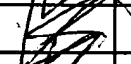










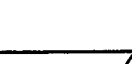
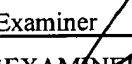
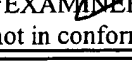
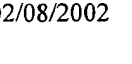

## INFORMATION DISCLOSURE STATEMENT

Applicants: Shunpei YAMAZAKI et al.

Filing Date: July 28, 1999

Group Art Unit: 2812

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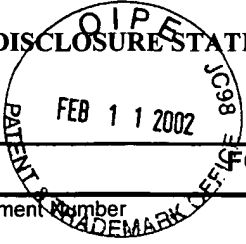

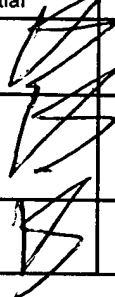
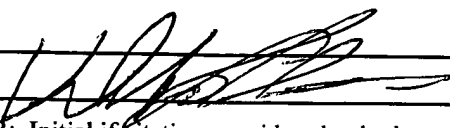
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TO-1449 (Rev. 8-83)		U.S. Department of Commerce Patent and Trademark Office		Atty Docket 0756-2011		Serial No. 09/362,192	
<b>INFORMATION DISCLOSURE STATEMENT</b> 				Applicants: Shunpei YAMAZAKI et al.			
				Filing Date: July 28, 1999		Group Art Unit: 2812	
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